

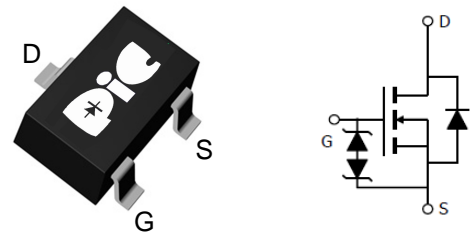
## ➤ General Description

This PAN0023ANS N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent  $R_{ds(On)}$  performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

## ➤ Feature

- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- ESD Protection Diode design-in
- SOT-23S package design

## ➤ SOT-23S



## ➤ Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- High saturation current capability. Direct Logic-Level Interface: TTL/CMOS
- Battery Operated Systems
- Solid-State Relays

## ➤ Absolute Maximum Ratings

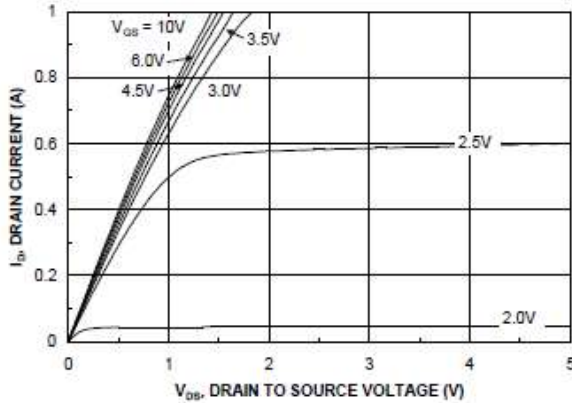
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	100	V
Gate -Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current( $T_J=150^\circ C$ )	$I_D$	$T_A=25^\circ C$	0.17
		$T_A=70^\circ C$	0.17
Pulsed Drain Current	$I_{DM}$	0.68	A
Continuous Source Current(Diode Conduction)	$I_S$	0.45	A
Power Dissipation	$P_D$	$T_A=25^\circ C$	1.25
		$T_A=70^\circ C$	0.8
Operating Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature Range	$T_{STG}$	-55/150	$^\circ C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ C/W$

➤ **Electrical Characteristics (T<sub>A</sub>=25°C Unless otherwise noted)**

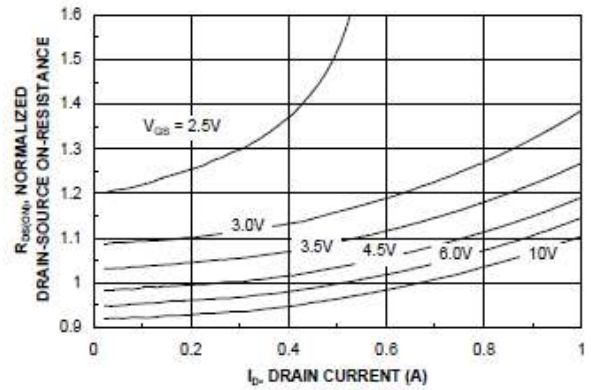
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.0	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			10	$\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=80V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=80V, V_{GS}=0V$ $T_J=85^\circ C$			10	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=0.17A$		4.0	5.8	$\Omega$
		$V_{GS}=4.5V, I_D=0.17A$		4.6	6.8	
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=0.17A$		0.8		S
Diode Forward Voltage	$V_{SD}$	$I_S=0.17A, V_{GS}=0V$		0.75	1.3	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=30V, V_{GS}=10V$ $I_D=0.22A$		1.8	3.5	nC
Gate-Source Charge	$Q_{gs}$			0.2		
Gate-Drain Charge	$Q_{gd}$			0.3		
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V$ $f=1MHz$		70		pF
Output Capacitance	$C_{oss}$			8		
Reverse Transfer Capacitance	$C_{rss}$			5		
Turn-On Time	$t_{d(on)}$	$V_{DD}=30V, R_G=50\Omega$ $I_D=0.28A, V_{GEN}=10V$		5	10	ns
	$t_r$			5	10	
Turn-Off Time	$t_{d(off)}$			7	15	
	$t_f$			10	20	

N-Ch 100V Fast Switching MOSFET  
 $V_{DS}=100V, I_D=0.17A, R_{DS(ON)}=5800m\Omega$

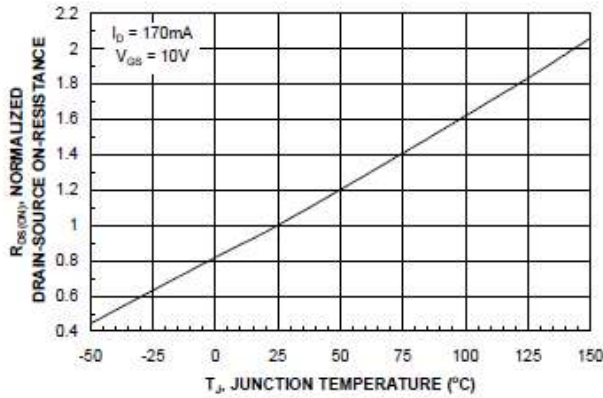
## ➤ Typical Characteristics



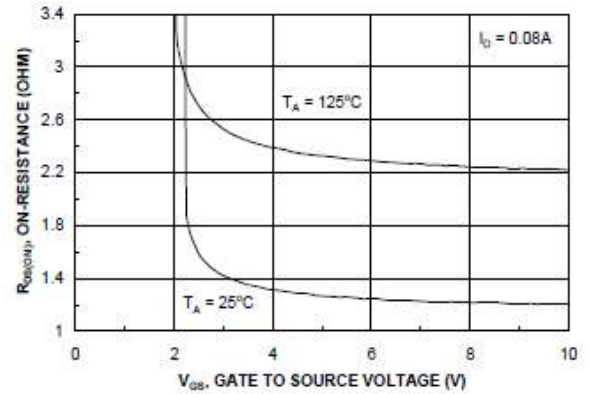
On-Region Characteristics



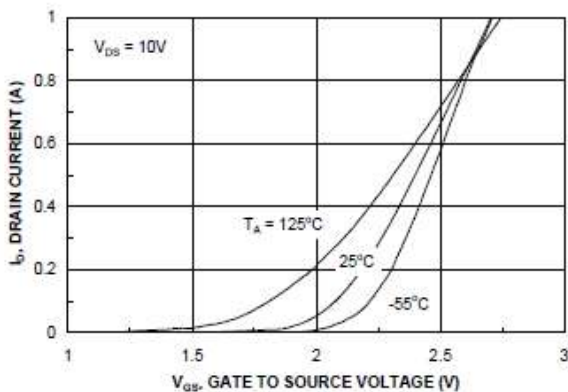
On-Resistance Variation with Drain Current and Gate Voltage



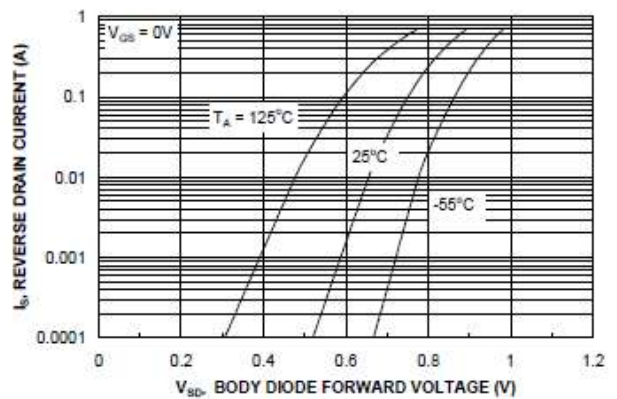
On-Resistance Variation with Temperature



On-Resistance Variation with Gate-to-Source Voltage

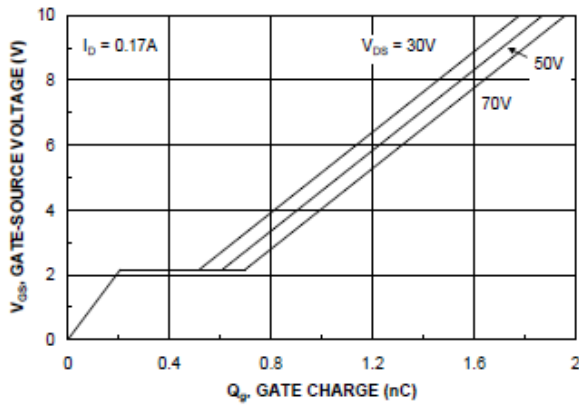


Transfer Characteristics

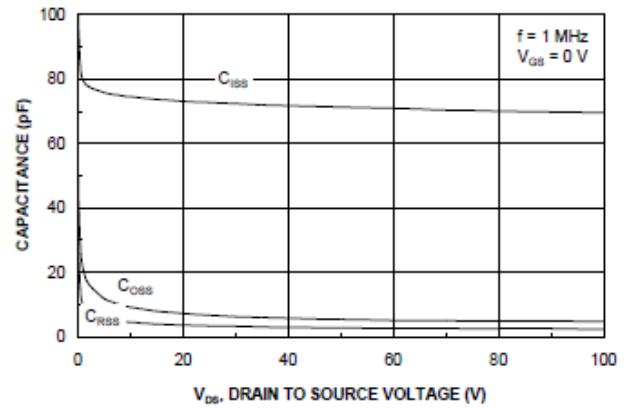


Body Diode Forward Voltage Variation with Source Current and Temperature

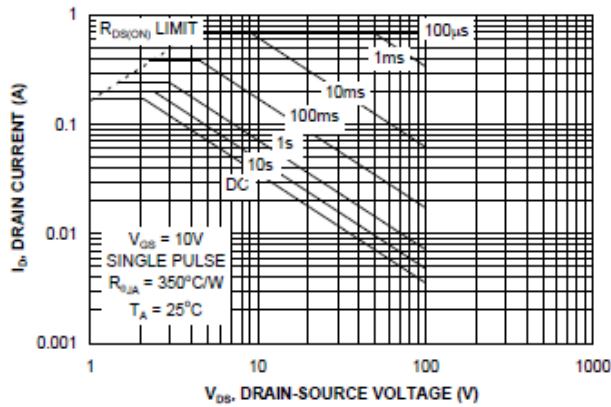
## N-Ch 100V Fast Switching MOSFET $V_{DS}=100V, I_D=0.17A, R_{DS(ON)}=5800m\Omega$



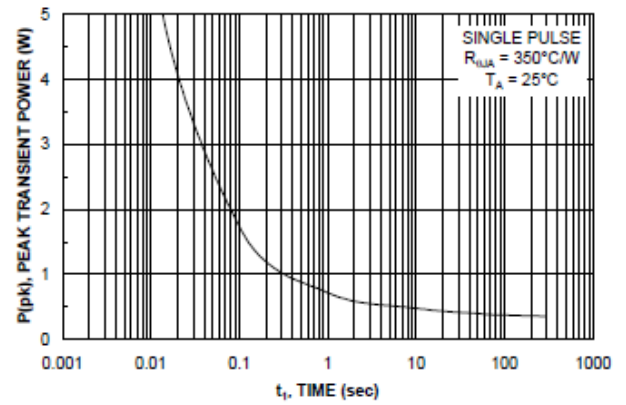
Gate Charge Characteristics



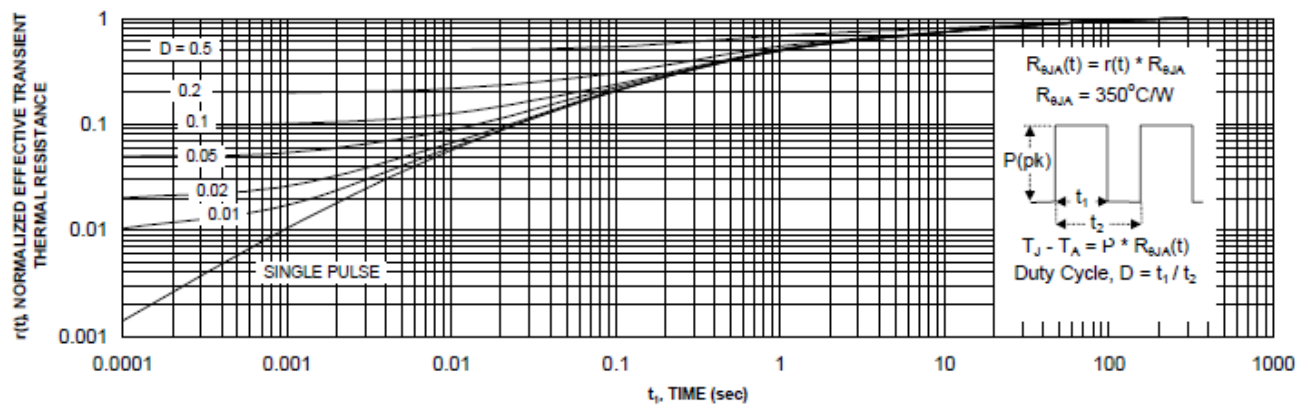
Capacitance Characteristics



Maximum Safe Operating Area

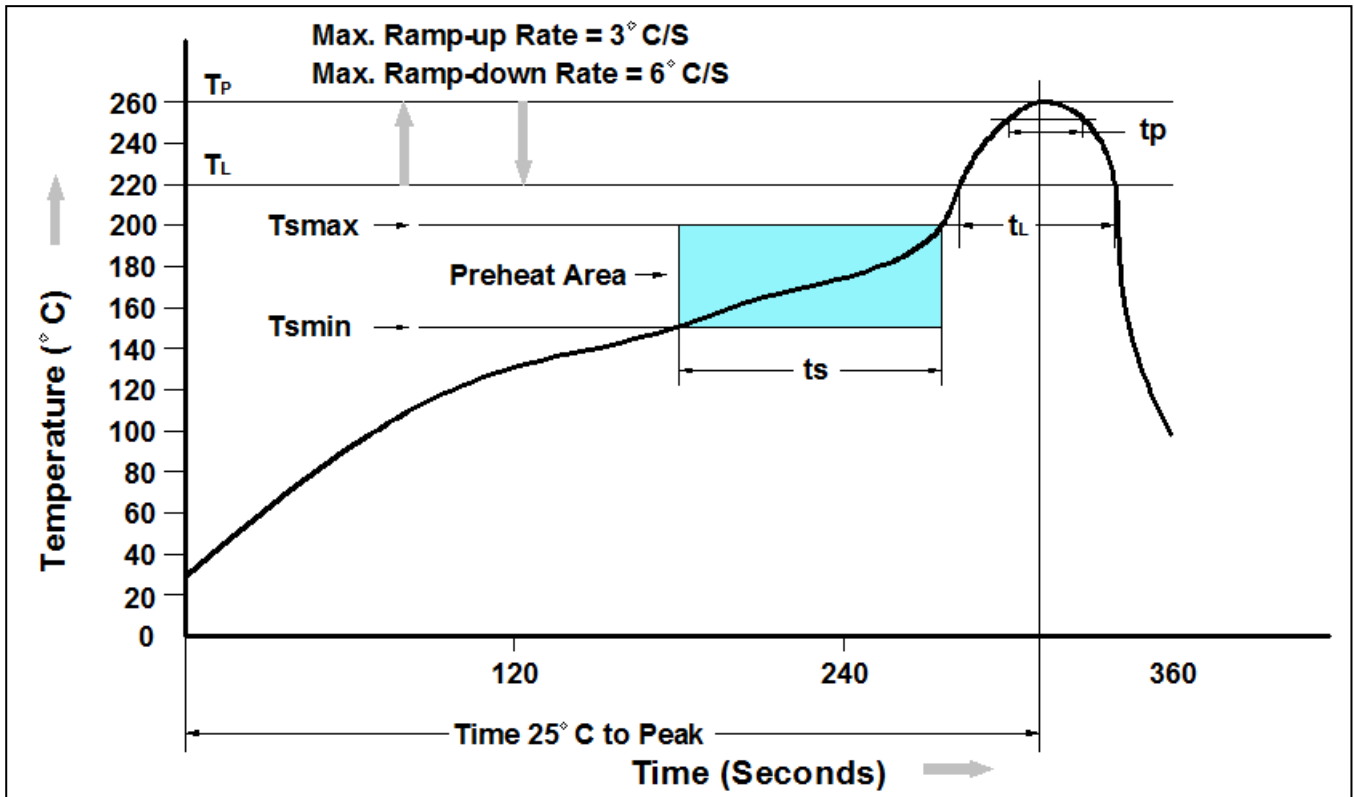


Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve, Junction to Ambient

➤ Recommand IR Reflow Soldering Thermal Profile

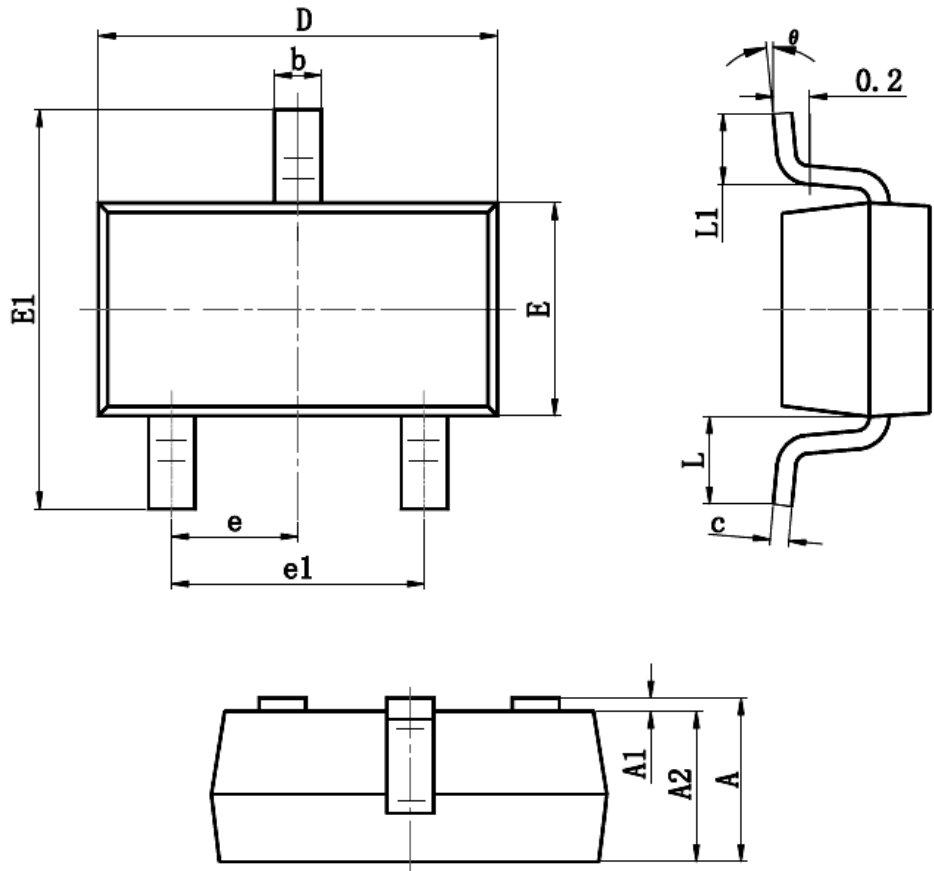


Profile Feature	Pb-Free Assembly Profile
Temperature Min. ( $T_{smin}$ )	150°C
Temperature Max. ( $T_{smax}$ )	200°C
Time ( $t_s$ ) from ( $T_{smin}$ to $T_{smax}$ )	60-120 seconds
Average Ramp-up Rate ( $t_L$ to $t_P$ )	3°C/second max.
Liquidous Temperature ( $T_L$ )	217°C
Time ( $t_L$ ) Maintained Above ( $T_L$ )	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time ( $t_P$ ) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate ( $T_P$ to $T_L$ )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN0023ANS	SOT-23S Reel	3000 pcs

➤ Package Information ( SOT-23S )



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
theta	0°	8°	0°	6°

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